Hex Buffers

The MC14049UB hex inverter/buffer is constructed with MOS P-channel and N-channel enhancement mode devices in a single monolithic structure. This complementary MOS device finds primary use where low power dissipation and/or high noise immunity is desired. This device provides logic-level conversion using only one supply voltage, V_{DD} . The input-signal high level (V_{IH}) can exceed the V_{DD} supply voltage for logic-level conversions. Two TTL/DTL Loads can be driven when the device is used as CMOS-to-TTL/DTL converters ($V_{DD} = 5.0 \ V, \ V_{OL} \leq 0.4 \ V, \ I_{OL} \geq 3.2 \ mA)$. Note that pins 13 and 16 are not connected internally on this device; consequently connections to these terminals will not affect circuit operation.

Features

- High Source and Sink Currents
- High-to-Low Level Converter
- Supply Voltage Range = 3.0 V to 18 V
- Meets JEDEC UB Specifications
- V_{IN} can exceed V_{DD}
- Improved ESD Protection on All Inputs
- These Devices are Pb-Free and are RoHS Compliant
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	-0.5 to +18.0	V
V _{in}	Input Voltage Range (DC or Transient)	-0.5 to +18.0	V
V _{out}	Output Voltage Range (DC or Transient)	-0.5 to V _{DD} +0.5	V
I _{in}	Input Current (DC or Transient) per Pin	±10	mA
l _{out}	Output Current (DC or Transient) per Pin	+45	mA
P _D	Power Dissipation, per Package (Note 1) Plastic SOIC	825 740	mW
T _A	Ambient Temperature Range	-55 to +125	°C
T _{stg}	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature (8–Second Soldering)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: All Packages: See Figure 4.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields referenced to the V_{SS} pin, only. Extra precautions must be taken to avoid applications of any voltage higher than the maximum rated voltages to this high–impedance circuit. For proper operation, the ranges $V_{SS} \leq V_{in} \leq 18 \ V$ and $V_{SS} \leq V_{out} \leq V_{DD}$ are recommended.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.



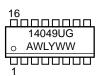
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MARKING DIAGRAMS



SOIC-16 D SUFFIX CASE 751B



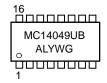


TSSOP-16 DT SUFFIX CASE 948F





SOEIAJ-16 F SUFFIX CASE 966



A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G or = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

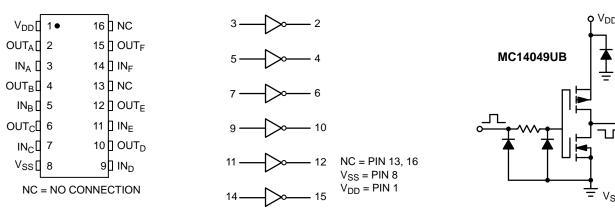


Figure 1. Pin Assignment

Figure 2. Logic Diagram MC14049UB

Figure 3. Circuit Schematic (1/6 of circuit shown)

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

			,,	- 55°C		25°C			125°C		
Characte	ristic	Symbol	V _{DD} Vdc	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
Output Voltage V _{in} = V _{DD} or 0	"0" Level	V _{OL}	5.0 10 15	- - -	0.05 0.05 0.05	- - -	0 0 0	0.05 0.05 0.05	- - -	0.05 0.05 0.05	Vdc
V _{in} = 0 or V _{DD}	"1" Level	V _{OH}	5.0 10 15	4.95 9.95 14.95	- - -	4.95 9.95 14.95	5.0 10 15	- - -	4.95 9.95 14.95	- - -	Vdc
Input Voltage $ (V_O = 4.5 \text{ Vdc}) $ $ (V_O = 9.0 \text{ Vdc}) $ $ (V_O = 13.5 \text{ Vdc}) $	"0" Level	V _{IL}	5.0 10 15	- - -	1.0 2.0 2.5	- - -	2.25 4.50 6.75	1.0 2.0 2.5	- - -	1.0 2.0 2.5	Vdc
$(V_O = 0.5 \text{ Vdc})$ $(V_O = 1.0 \text{ Vdc})$ $(V_O = 1.5 \text{ Vdc})$	"1" Level	V _{IH}	5.0 10 15	4.0 8.0 12.5	- - -	4.0 8.0 12.5	2.75 5.50 8.25	- - -	4.0 8.0 12.5	- - -	Vdc
Output Drive Current (V _{OH} = 2.5 Vdc) (V _{OH} = 9.5 Vdc) (V _{OH} = 13.5 Vdc)	Source	ІОН	5.0 10 15	- 1.6 - 1.6 - 4.7	- - -	- 1.25 - 1.3 - 3.75	- 2.5 - 2.6 - 10	- - -	- 1.0 - 1.0 - 3.0	- - -	mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	Sink	I _{OL}	5.0 10 15	3.75 10 30	- - -	3.2 8.0 24	6.0 16 40	- - -	2.6 6.6 19	- - -	mAdc
Input Current		I _{in}	15	-	± 0.1	-	±0.000 01	± 0.1	-	± 1.0	μAdc
Input Capacitance (V _{in} = 0)	C _{in}	-	-	-	-	10	20	-	-	pF
Quiescent Current (Per Pa	ckage)	I _{DD}	5.0 10 15	- - -	1.0 2.0 4.0	- - -	0.002 0.004 0.006	1.0 2.0 4.0	- - -	30 60 120	μAdc
Total Supply Current (Note 3 and 4) (Dynamic plus Quiescent, Per Package) (C _L = 50 pF on all outputs, all buffers switching)		I _T	5.0 10 15			$I_T = (3.$	- 8 μΑ/kHz) f 5 μΑ/kHz) f 3 μΑ/kHz) f	+ I _{DD}	•		μAdc

^{2.} Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

where: I_T is in μA (per package), C_L in pF, $V = (V_{DD} - V_{SS})$ in volts, f in kHz is input frequency, and k = 0.002.

^{3.} The formulas given are for the typical characteristics only at 25°C.

^{4.} To calculate total supply current at loads other than 50 pF:

SWITCHING CHARACTERISTICS (Note 5) ($C_L = 50 \text{ pF}, T_A = 25^{\circ}\text{C}$)

Characteristic	Symbol	V _{DD} Vdc	Min	Typ (Note 6)	Max	Unit
Output Rise Time	t _{TLH}					ns
$t_{TLH} = (0.8 \text{ ns/pF}) C_L + 60 \text{ ns}$		5.0	_	100	160	
$t_{TLH} = (0.3 \text{ ns/pF}) C_L + 35 \text{ ns}$		10	-	50	100	
$t_{TLH} = (0.27 \text{ ns/pF}) C_L + 26.5 \text{ ns}$		15	_	40	60	
Output Fall Time	t _{THL}					ns
$t_{THL} = (0.3 \text{ ns/pF}) C_L + 25 \text{ ns}$		5.0	_	40	60	
$t_{THL} = (0.12 \text{ ns/pF}) C_L + 14 \text{ ns}$		10	_	20	40	
$t_{THL} = (0.1 \text{ ns/pF}) C_L + 10 \text{ ns}$		15	-	15	30	
Propagation Delay Time	t _{PLH}					ns
$t_{PLH} = (0.38 \text{ ns/pF}) C_L + 61 \text{ ns}$		5.0	_	80	120	
$t_{PLH} = (0.20 \text{ ns/pF}) C_L + 30 \text{ ns}$		10	_	40	65	
$t_{PLH} = (0.11 \text{ ns/pF}) C_L + 24.5 \text{ ns}$		15	_	30	50	
Propagation Delay Time	t _{PHL}					ns
$t_{PHL} = (0.38 \text{ ns/pF}) C_L + 11 \text{ ns}$		5.0	_	30	60	
$t_{PHL} = (0.12 \text{ ns/PF}) C_L + 9 \text{ ns}$		10	_	15	30	
$t_{PHL} = (0.11 \text{ ns/pF}) C_L + 4.5 \text{ ns}$		15	_	10	20	

ORDERING INFORMATION

Device	Package	Shipping [†]		
MC14049UBDG	SOIC-16	48 Units / Rail		
NLV14049UBDG*	(Pb-Free)			
MC14049UBDR2G	SOIC-16	2500 / Tape & Reel		
NLV14049UBDR2G*	(Pb-Free)			
MC14049UBDTR2G	TSSOP-16 (Pb-Free)	2500 / Tape & Reel		
MC14049UBFELG	SOEIAJ-16 (Pb-Free)	2000 / Tape & Reel		

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

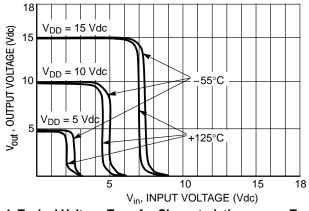


Figure 4. Typical Voltage Transfer Characteristics versus Temperature

^{5.} The formulas given are for the typical characteristics only at 25°C.6. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

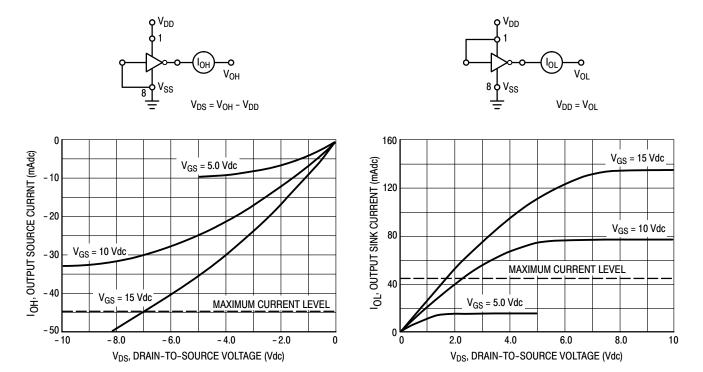


Figure 5. Typical Output Source Characteristics

Figure 6. Typical Output Sink Characteristics

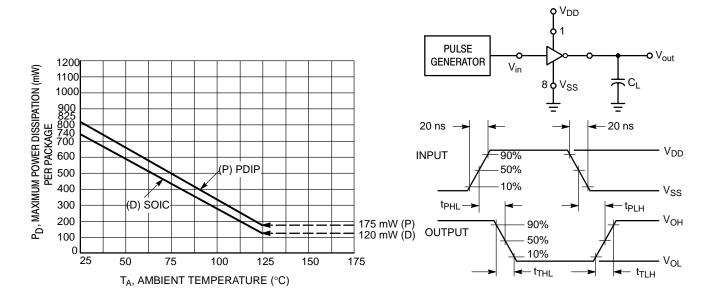
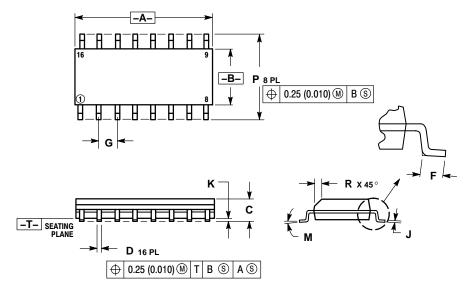


Figure 7. Ambient Temperature Power Derating

Figure 8. Switching Time Test Circuit and Waveforms

PACKAGE DIMENSIONS

SOIC-16 **D SUFFIX** CASE 751B-05 ISSUE K



NOTES:

- NOTES:

 1 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

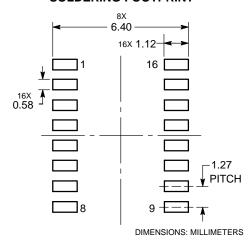
 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- MAXIMUM MOLD PHO HUSION 0.15 (0.006) PER SIDE DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MIN MAX		MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
P	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

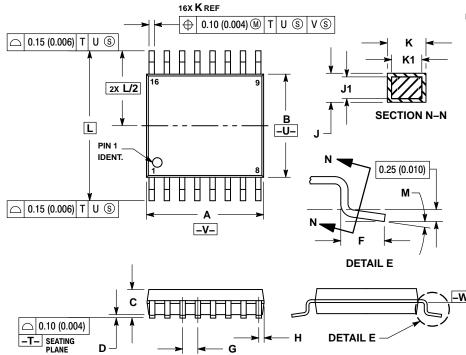
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSSOP-16 **DT SUFFIX** CASE 948F **ISSUE B**



D

- NOTES:

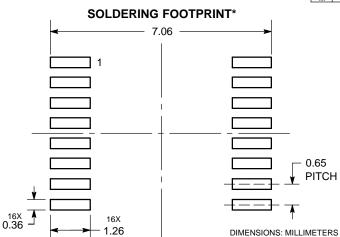
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.06) DEP. SIDE. EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE

 - 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 - 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

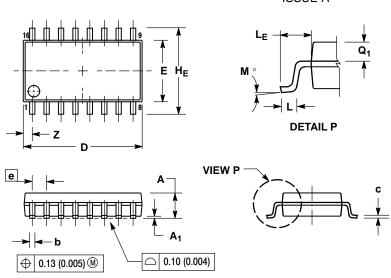
	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252 BSC		
М	0°	8°	0°	8 °	



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOEIAJ-16 **F SUFFIX CASE 966 ISSUE A**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE
 MEASURED AT THE PARTING LINE, MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

 THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	-	2.05		0.081	
A ₁	0.05	0.20	0.002	0.008	
b	0.35	0.50	0.014	0.020	
C	0.10	0.20	0.007	0.011	
D	9.90	10.50	0.390	0.413	
Е	5.10	5.45	0.201	0.215	
е	1.27	BSC	0.050 BSC		
HE	7.40	8.20	0.291	0.323	
L	0.50	0.85	0.020	0.033	
LE	1.10	1.50	0.043	0.059	
M	0 °	10 °	0 °	10°	
Q ₁	0.70	0.90	0.028	0.035	
Z		0.78		0.031	

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